General Purpose Sensitive Gate Silicon Controlled Rectifier Reverse Blocking Thyristor

PNPN device designed for line-powered general purpose applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in a cost effective plastic TO-226AA package.

Features

- Sensitive Gate Allows Direct Triggering by Microcontrollers and Other Logic Circuits
- On-State Current Rating of 0.8 Amperes RMS at 80°C
- Surge Current Capability 10 Amperes
- Immunity to dV/dt 20 V/µsec Minimum at 110°C
- Glass-Passivated Surface for Reliability and Uniformity
- This is a Pb–Free Device

MAXIMUM RATINGS (T_J = 25° C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1.) $(T_J = -40 \text{ to } 110^{\circ}\text{C}, \text{ Sine Wave, } 50 \text{ to}$ 60 Hz; Gate Open)	V _{DRM,} V _{RRM}	400	Volts
On-State RMS Current (T _C = 80°C) 180° Conduction Angles	I _{T(RMS)}	0.8	Amp
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, T _J = 25°C)	I _{TSM}	10	Amps
Circuit Fusing Consideration (t = 10 ms)	l ² t	0.415	A ² s
Forward Peak Gate Power $(T_A = 25^{\circ}C, Pulse Width \le 1.0 \mu s)$	P _{GM}	0.1	Watt
Forward Average Gate Power (T _A = 25°C, t = 20 ms)	P _{G(AV)}	0.10	Watt
Forward Peak Gate Current $(T_A = 25^{\circ}C, Pulse Width \le 1.0 \mu s)$	I _{GM}	1.0	Amp
Reverse Peak Gate Voltage $(T_A = 25^{\circ}C, Pulse Width \le 1.0 \mu s)$	V _{GRM}	5.0	Volts
Operating Junction Temperature Range @ Rate V _{RRM} and V _{DRM}	TJ	–40 to 110	°C
Storage Temperature Range	T _{stg}	–40 to 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

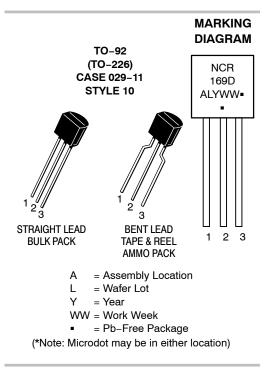


ON Semiconductor®

http://onsemi.com

SCR 0.8 AMPERES RMS 400 VOLTS





PIN ASSIGNMENT				
1 Cathode				
2	Gate			
3	Anode			

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Semiconductor Components Industries, LLC, 2012 October, 2012 – Rev. 2

THERMAL CHARACTERISTICS

Characteristic			Symbol		Max	Unit	
Thermal Resistance – Junction to Case – Junction to Ambient				75 200	o	°C/W	
Lead Solder Temperature (<1/16" from case, 10 secs max)			ΤL		260		°C
ELECTRICAL CHARACTERISTICS (T _C = 25° C ur	nless otherwise noted)	1					
Characteristic		Sym	bol	Min	Тур	Max	Unit
OFF CHARACTERISTICS							
Peak Repetitive Forward or Reverse Blocking Current (Note 1.) (V_D = Rated V_{DRM} and V_{RRM} ; R_{GK} = 1.0 k Ω)	T _C = 25°C T _C = 110°C	I _{DRM} ,	I _{RRM}			10 0.1	μA mA
ON CHARACTERISTICS					•		
Peak Forward On–State Voltage ^(*) (I _{TM} = 1.0 Amp Peak @ T _A = 25°C)		V _T	М	-	-	1.7	Volts
Gate Trigger Current (Continuous dc) (Note 2.) $(V_{AK} = 12 \text{ V}, \text{ R}_{L} = 100 \text{ Ohms})$	$T_{C} = 25^{\circ}C$	ا _G .	Т	-	40	200	μA
Holding Current (Note 2.) $(V_{AK} = 12 \text{ V}, I_{GT} = 0.5 \text{ mA})$	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$	I _H		-	0.5 -	5.0 10	mA
Latch Current (V _{AK} = 12 V, I _{GT} = 0.5 mA, R _{GK} = 1.0 k)	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$	ار		-	0.6 -	10 15	mA
Gate Trigger Voltage (Continuous dc) (Note 2.) $(V_{AK} = 12 \text{ V}, \text{ R}_{L} = 100 \text{ Ohms}, \text{ I}_{GT} = 10 \text{ mA})$	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$	V _G	T		0.62	0.8 1.2	Volts

DYNAMIC CHARACTERISTICS

Critical Rate of Rise of Off–State Voltage $(V_D = Rated V_{DRM}, Exponential Waveform, R_{GK} = 1000 Ohms, T_J = 110°C)$	dV/dt	20	35	-	V/μs
Critical Rate of Rise of On–State Current (I _{PK} = 20 A; Pw = 10 μsec; diG/dt = 1.0 A/μsec, Igt = 20 mA)	di/dt	-	-	50	A/µs

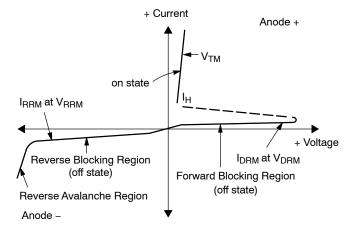
*Indicates Pulse Test: Pulse Width \leq 1.0 ms, Duty Cycle \leq 1%.

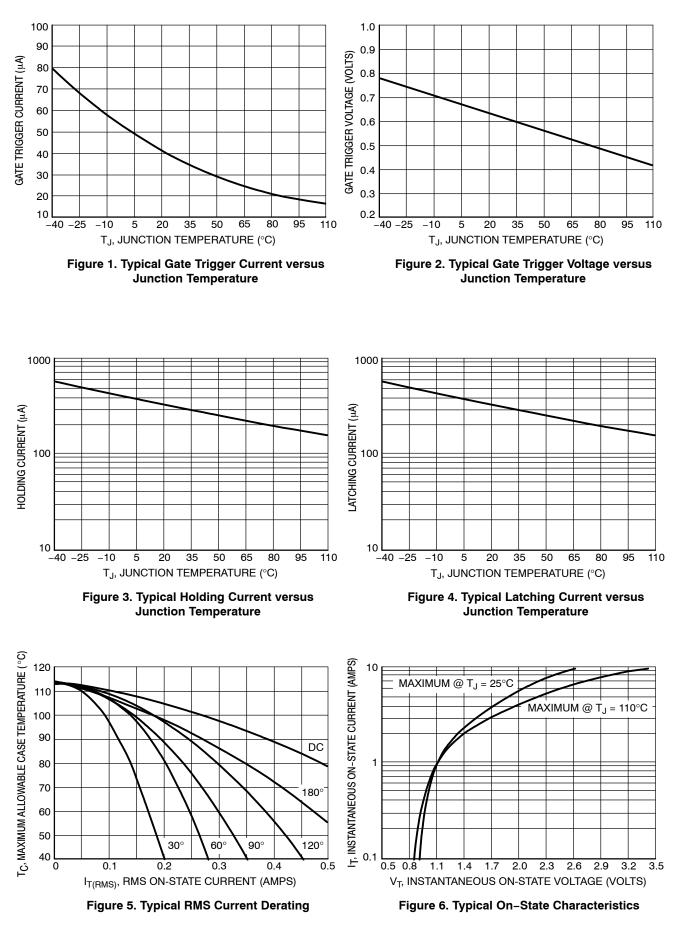
1. R_{GK} = 1000 Ohms included in measurement.

2. Does not include R_{GK} in measurement.

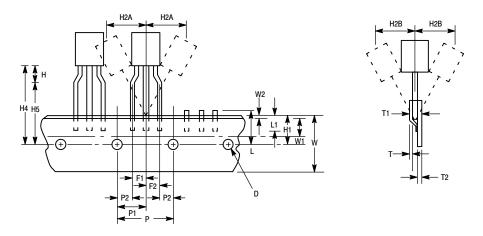
Voltage Current Characteristic of SCR

Symbol	Parameter	
V _{DRM}	Peak Repetitive Off State Forward Voltage	
I _{DRM}	Peak Forward Blocking Current	
V _{RRM}	Peak Repetitive Off State Reverse Voltage	
I _{RRM}	Peak Reverse Blocking Current	
V _{TM}	Peak on State Voltage	
Ι _Η	Holding Current	





TO-92 EIA RADIAL TAPE IN FAN FOLD BOX OR ON REEL



		Specification			
		Inches Millimete		neter	
Symbol	Item	Min	Max	Min	Max
D	Tape Feedhole Diameter	0.1496	0.1653	3.8	4.2
D2	Component Lead Thickness Dimension	0.015	0.020	0.38	0.51
F1, F2	Component Lead Pitch	0.0945	0.110	2.4	2.8
Н	Bottom of Component to Seating Plane	.059	.156	1.5	4.0
H1	Feedhole Location	0.3346	0.3741	8.5	9.5
H2A	Deflection Left or Right	0	0.039	0	1.0
H2B	Deflection Front or Rear	0	0.051	0	1.0
H4	Feedhole to Bottom of Component	0.7086	0.768	18	19.5
H5	Feedhole to Seating Plane	0.610	0.649	15.5	16.5
L	Defective Unit Clipped Dimension	0.3346	0.433	8.5	11
L1	Lead Wire Enclosure	0.09842	-	2.5	-
Р	Feedhole Pitch	0.4921	0.5079	12.5	12.9
P1	Feedhole Center to Center Lead	0.2342	0.2658	5.95	6.75
P2	First Lead Spacing Dimension	0.1397	0.1556	3.55	3.95
Т	Adhesive Tape Thickness	0.06	0.08	0.15	0.20
T1	Overall Taped Package Thickness	-	0.0567	-	1.44
T2	Carrier Strip Thickness	0.014	0.027	0.35	0.65
W	Carrier Strip Width	0.6889	0.7481	17.5	19
W1	Adhesive Tape Width	0.2165	0.2841	5.5	6.3
W2	Adhesive Tape Position	.0059	0.01968	.15	0.5

NOTES:

1. Maximum alignment deviation between leads not to be greater than 0.2 mm.

2. Defective components shall be clipped from the carrier tape such that the remaining protrusion (L) does not exceed a maximum of 11 mm.

3. Component lead to tape adhesion must meet the pull test requirements.

4. Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.

5. Holddown tape not to extend beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.

6. No more than 1 consecutive missing component is permitted.

7. A tape trailer and leader, having at least three feed holes is required before the first and after the last component.

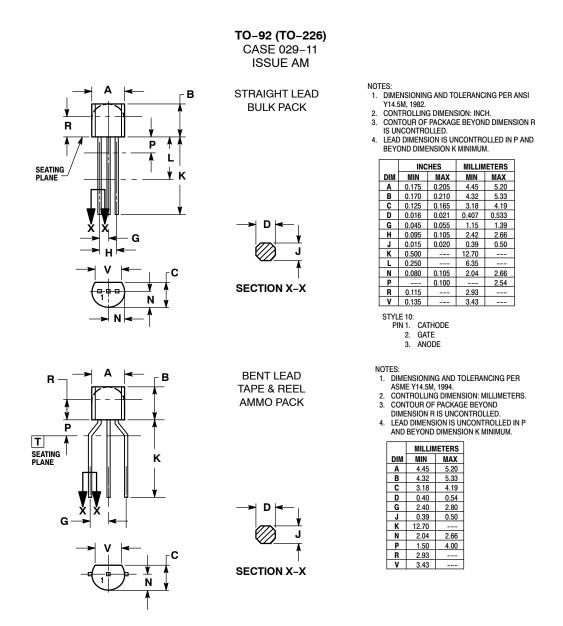
8. Splices will not interfere with the sprocket feed holes.

ORDERING & SHIPPING INFORMATION: MCR100 Series packaging options, Device Suffix

Device	Description of TO92 Tape Orientation	Shipping
NCR169DG	N/A, Bulk	Bulk in Box (5K/Box) (Pb-Free)
NCR169DRLRAG	Round side of TO92 and adhesive tape visible	Radial Tape and Reel (2K/Reel) (Pb-Free)

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS



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